

Silicon PNP Power Transistors 2N5621 2N5623 2N5625 2N5627

DESCRIPTION

- With TO-3 package
- Excellent safe operating area
- Low collector-emitter saturation voltage

APPLICATIONS

- For audio and general-purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

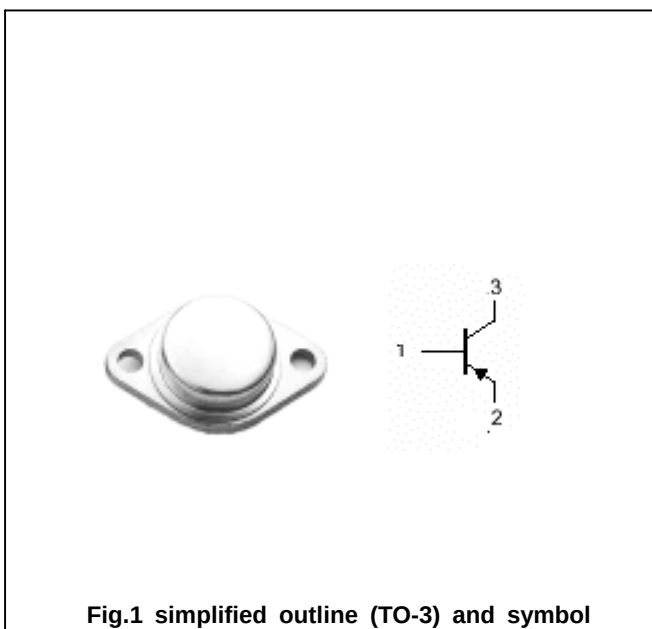


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = ^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5621	Open emitter	60	V
		2N5623/5625		80	
		2N5627		100	
V_{CEO}	Collector-emitter voltage	2N5621	Open base	80	V
		2N5623/5625		100	
		2N5627		120	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			10	A
P_D	Total power dissipation		$T_C = 25^\circ\text{C}$	100	W
T_j	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature			-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.5	$^\circ\text{C/W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter sustaining voltage	2N5621	I _C =50mA ; I _B =0	60			V
		2N5623/5625		80			
		2N5627		100			
V _{CEsat}	Collector-emitter saturation voltage		I _C =5A; I _B =0.5A			2.0	V
V _{BE}	Base-emitter on voltage		I _C =5A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =Rated V _{CBO} ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	2N5621/5625	I _C =5A ; V _{CE} =5V	70		200	
		2N5623/5627		30		90	
f _T	Transition frequency	2N5621/5625	I _C =1A ; V _{CE} =12V	40			MHz
		2N5623/5627		30			

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PACKAGE OUTLINE

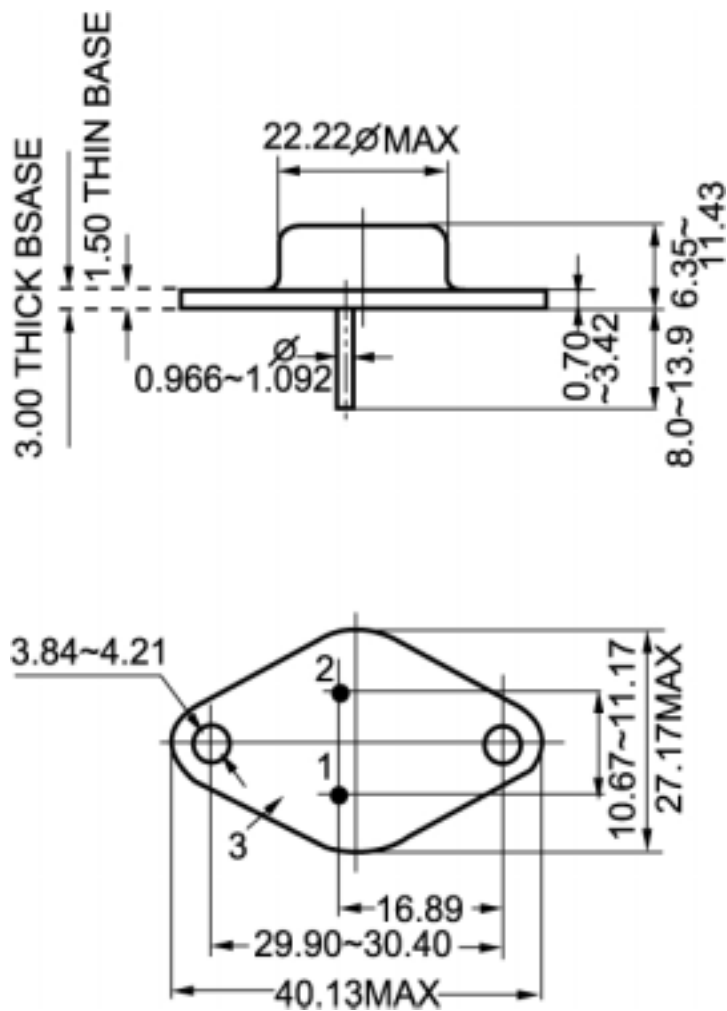


Fig.2 outline dimensions